

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MICRON.079DV1 C 1	APPLICATION NO. 08/079,984 <i>Unknown</i>
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Gonzalez et al.	
		FILING DATE <i>June 12, 2004</i>	GROUP <i>Herewith</i> Unknown

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
<i>PF</i>	6,033,998	03/07/00	Aronowitz et al.			03/09/98
	6,037,224	03/14/00	Buller et al.			05/02/97
<i>✓</i>	6,110,842	06/29/00	Okuno et al.			04/22/98

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EXAMINER <i>John Krol</i>	DATE CONSIDERED <i>2/11/05</i>
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON 0794VIC1	APPLICATION NO. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Gonzalez et al.	
(USE SEVERAL SHEETS IF NECESSARY)		FILING DATE Herewith	GROUP Unknown

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	4,827,153	12/9/88	Masuoka			
	4,651,406	3/24/87	Shimizu et al.			
	4,957,878	9/18/90	Lowrey et al.			
	4,875,982	6/30/87	Noble, Jr. et al.			
	5,057,449	10/15/91	Lowrey et al.			
	5,264,724	11/23/93	Brown et al.			
	5,358,894	10/25/94	Fazan et al.			
	5,360,769	11/1/94	Thakur et al.			
	5,376,593	12/27/94	Sandhu et al.			
	5,393,683	2/28/95	Mathews et al.			
	5,405,791	4/11/95	Ahmad et al.			
	5,407,870	4/18/95	Okada et al.			
	5,483,234	10/31/95	Toriumi et al.			
	5,502,009	3/26/96	Lin			
	5,668,035	9/16/97	Fang et al.			
	5,683,819	1/26/99	Gonzalez			
	5,966,818	10/12/99	Sun et al.			

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	S. Shimizu, et al., "Impact of Surface Proximity Gettering and Nitrided Oxide Side-Wall Spacer by Nitrogen Implantation on Sub-Quarter Micron CMOS LDD FETs," IEDM 1995, pp. 859-862

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EXAMINER	DATE CONSIDERED
<i>John Gonzalez</i>	2/11/05

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 608/DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.